

SANYO	No.544G	2SA1011/2SC2344
PNP/NPN Epitaxial Planar Silicon Transistors High-Voltage Switching, AF Power Amp, 100W Output Predriver Applications		

() : 2SA1011

Maximum Ratings at Ta=25°C

			unit
Collector-to-Base Voltage	V _{CB0}	(-) 180	V
Collector-to-Emitter Voltage	V _{CEO}	(-) 160	V
Emitter-to-Base Voltage	V _{EBO}	(-) 6	V
Collector Current	I _C	(-) 1.5	A
Collector Current (Pulse)	I _{CP}	(-) 3	A
Collector Dissipation	P _C	25	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	- 55 to + 150	°C

T_c=25°C

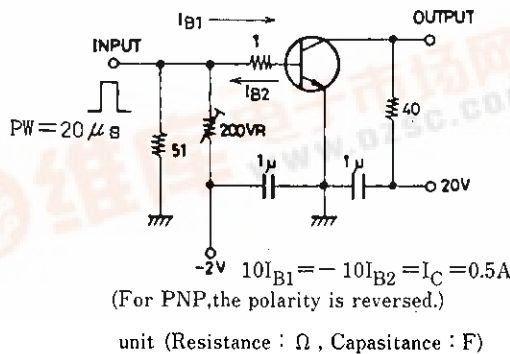
Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	I _{CB0}	V _{CB} = (-) 120V, I _E = 0			(-) 10	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} = (-) 4V, I _C = 0			(-) 10	μA
DC Current Gain	h _{FE}	V _{CE} = (-) 5V, I _C = (-) 300mA	60 ※		200 ※	
Gain-Bandwidth Product	f _T	V _{CE} = (-) 10V, I _C = (-) 50mA		100		MHz
Output Capacitance	C _{ob}	V _{CB} = (-) 10V, f = 1MHz		(30)		pF
				23		pF
Base-to-Emitter Voltage	V _{BE}	V _{CE} = (-) 5V, I _C = (-) 10mA	(-) 1.5			V
C-E Saturation Voltage	V _{CE(sat)}	I _C = (-) 500mA, I _B = (-) 50mA	(- 0.5)			V
			0.3			V
C-B Breakdown Voltage	V _{(BR) CBO}	I _C = (-) 1mA, I _E = 0	(-) 180			V
C-E Breakdown Voltage	V _{(BR) CEO}	I _C = (-) 1mA, I _{BE} = ∞	(-) 160			V
E-B Breakdown Voltage	V _{(BR) EBO}	I _E = (-) 1mA, I _C = 0	(-) 6			V
Turn-ON Time	t _{on}	See specified Test Circuit.	(0.29)	0.15		μs
Fall Time	t _f	"	(0.19)	0.48		μs
Storage Time	t _{stg}	"	(0.48)	0.81		μs

※ The 2SA1011/2SC2344 are classified by 300mA h_{FE} as follows :

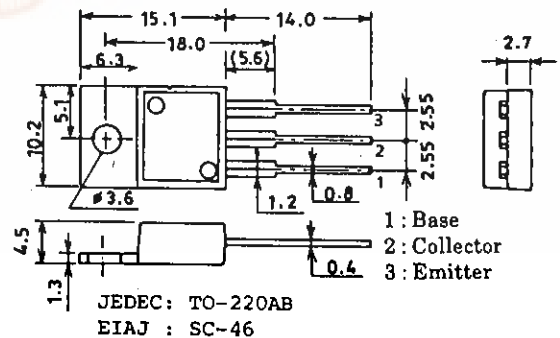
60	D	120	100	E	200
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Switching Time Test Circuit

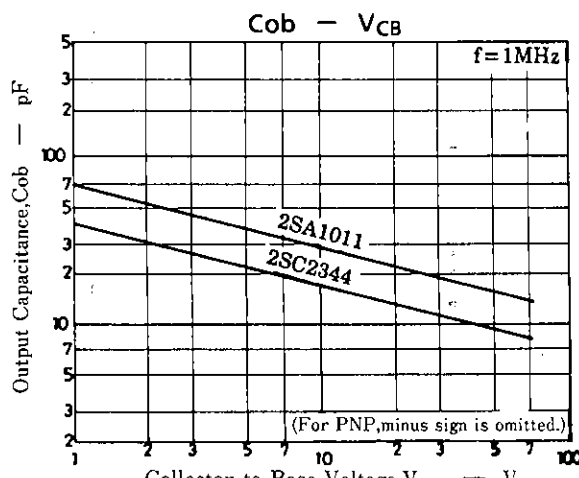
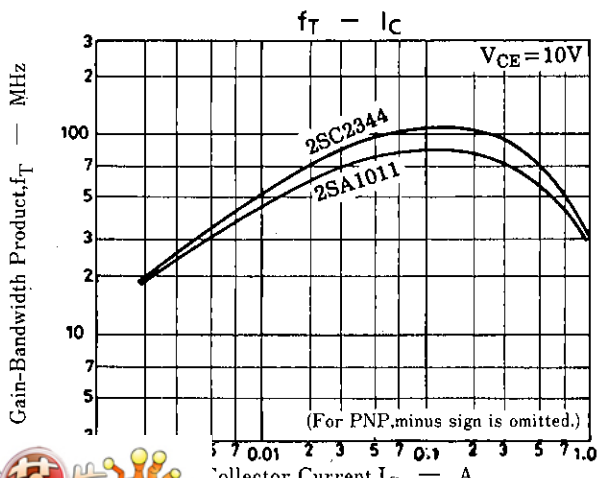
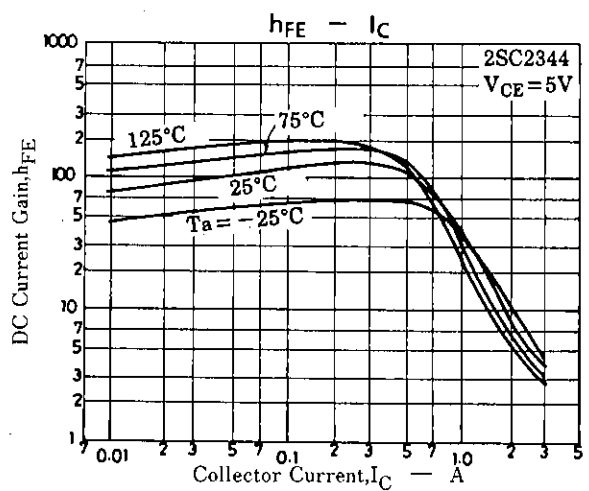
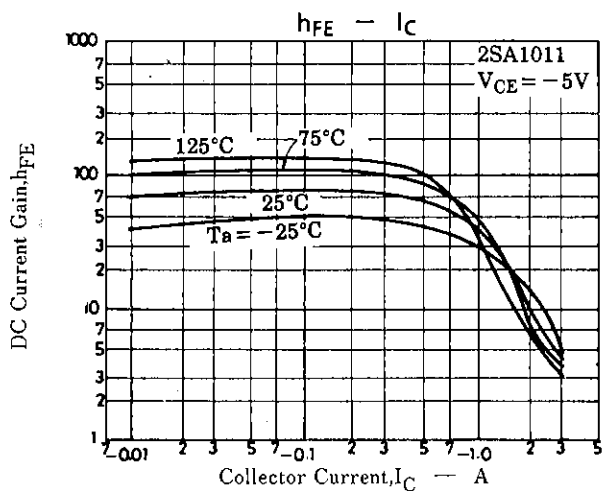
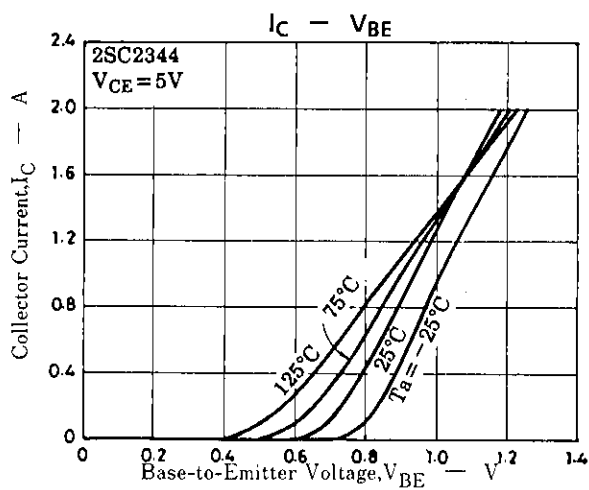
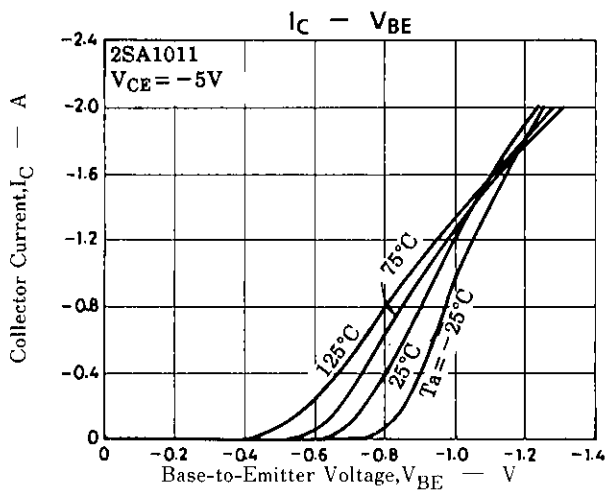
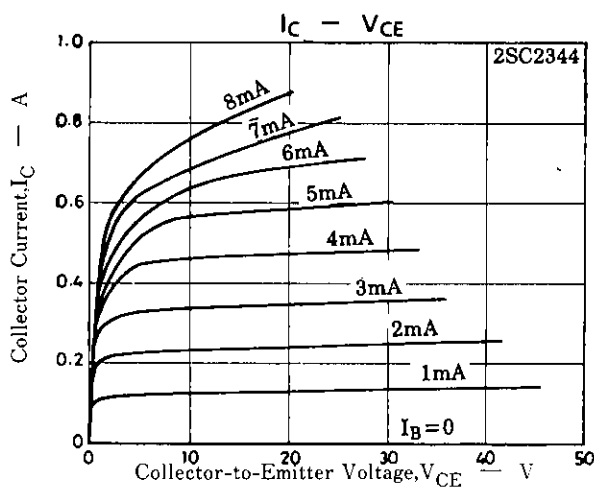
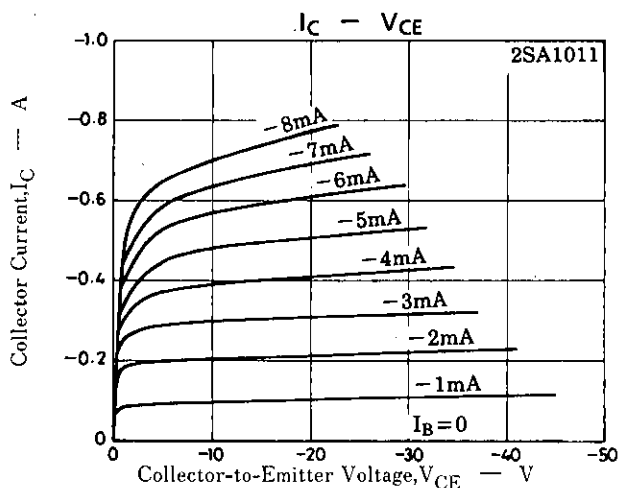


Package Dimensions 2010C

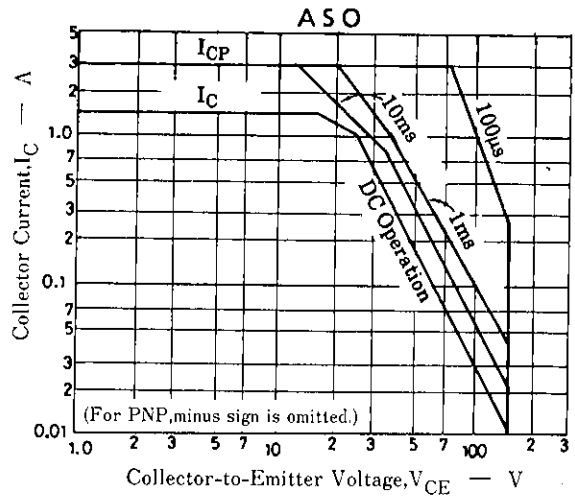
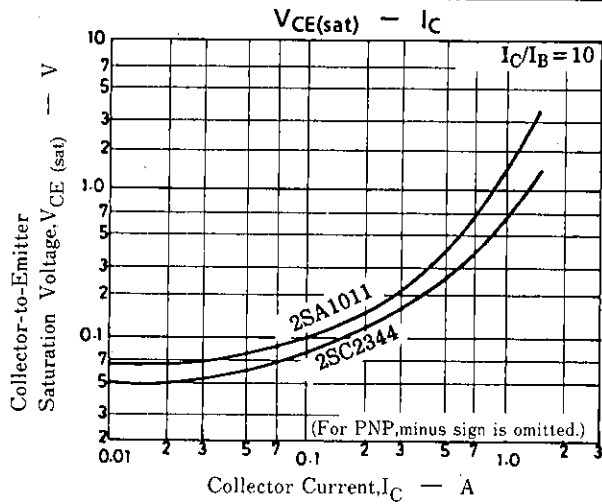
(unit : mm)



2SA1011/2SC2344



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